

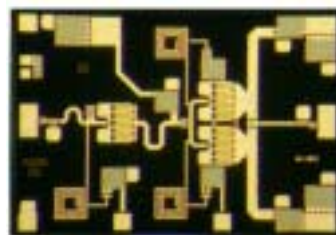
Preliminary

## 14 – 18 GHz 26dBm Driver MMIC

### FEATURES

- $P_{1dB}$ : 26 dBm
- Small Signal Gain: 12 dB
- Bias Condition: 350 mA @ 8 V

### PHOTO ENLARGEMENT

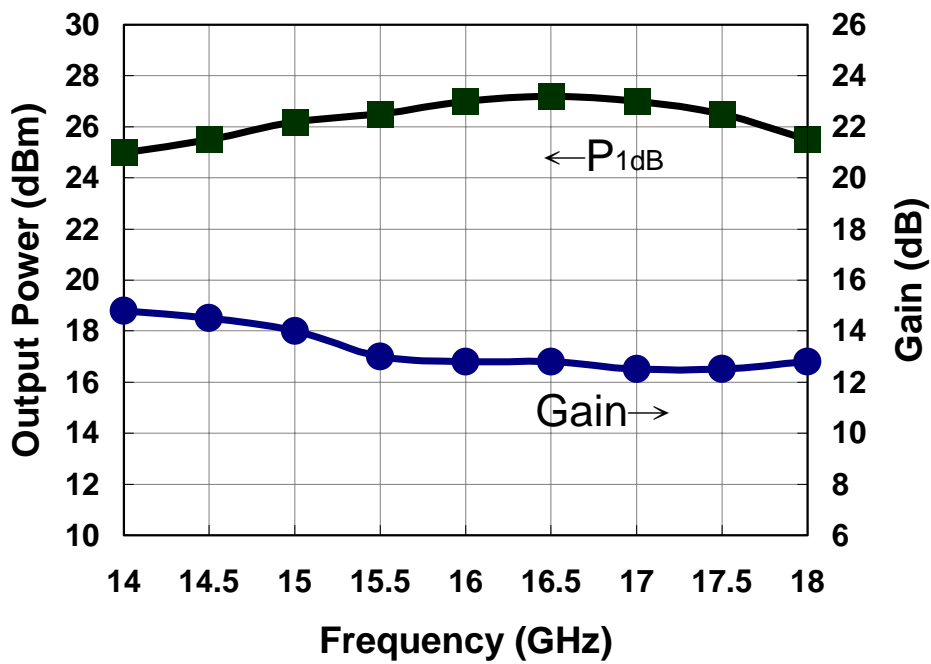


### DESCRIPTION

The TC1952 is a two stages PHEMT high power amplifier MMIC that operates from 14 to 18 GHz. The amplifier provides a typical 12 dB of gain and delivers 26 dBm of  $P_{1dB}$ . The MMIC is fabricated using Transcom's proprietary matured GaAs PHEMT process. The process features full passivation for increased performance and reliability. All devices are 100 % DC tested to assure consistent quality. Bond pads are gold plated for either thermocompression or thermosonic wire bonding. Backside gold plating is compatible with standard AuSn die-attach.

### ELECTRICAL SPECIFICATIONS ( $T_a = 25\text{ }^\circ\text{C}$ )

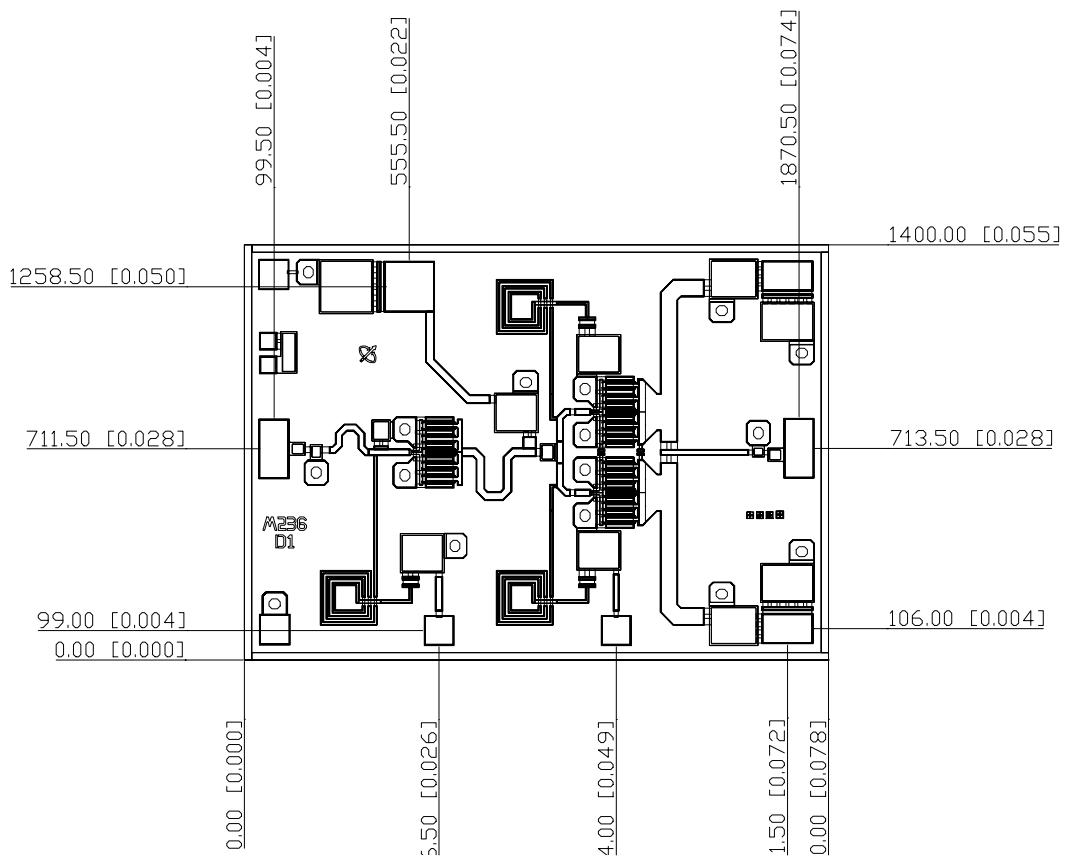
SYMBOL	DESCRIPTION	MIN	TYP	MAX	UNITS
<b>FREQ</b>	Frequency Range	14		18	GHz
<b>SSG</b>	Small Signal Gain		12		dB
<b>P1dB</b>	Output Power at 1dB Gain Compression		26		dBm
<b>VSWR, IN</b>	Input VSWR		2.5:1		-
<b>VSWR, OUT</b>	Output VSWR		2.5:1		-
<b>VDD</b>	Supply Voltage		8		Volt
<b>Vg</b>	Gate Voltage		-0.8		Volt
<b>IDD</b>	Bias Current Without RF		350		mA
<b>IDRF</b>	Current Supply @ $P_{1dB}$		380		mA

**TYPICAL CHARACTERISTICS**
Pout VS Freq. & Gain VS Freq.


**MECHANICAL OUTLINE**

Units: micrometer (inch)

Thickness: 76.2 (0.003)

 Chip Size:  $\pm 50.8$  (0.002)


**ASSEMBLY DIAGRAM**